

ABSTRACT

Provided are a substrate control device and a semiconductor reaction chamber. The substrate control device comprises a substrate supporting portion, a first driving portion, a second driving portion, and a bottom tray, wherein the substrate supporting portion is used to support a substrate; the first driving portion is disposed below the substrate supporting portion and used to drive the substrate supporting portion to rotate within the horizontal plane, and a hollow region is formed inside the first driving portion; the second driving portion includes a tubular portion and a rod portion, the tubular portion is disposed inside the hollow region, one end of the rod portion is disposed inside the tubular portion, the other end of the rod portion is fixedly mounted on the bottom tray, and the second driving portion is configured to drive the tubular portion to lift and lower along the rod portion, so as to drive the substrate supporting portion and the first driving portion to lift and lower in the vertical direction. The substrate control device of the present application is compact in size, easy to install, and suitable for semiconductor apparatuses with constrained space.